

Title (en)

A method of manufacturing a semiconductor device.

Title (de)

Verfahren zur Herstellung einer Halbleitervorrichtung.

Title (fr)

Procédé de fabrication d'un dispositif semiconducteur.

Publication

EP 0023775 A1 19810211 (EN)

Application

EP 80302336 A 19800710

Priority

JP 8766979 A 19790711

Abstract (en)

A layer (2) formed on a semiconductor substrate (1) has a projection or epitaxial rock (4) thereon. To remove the projection (4) an etch resistant membrane (3) is formed over the layer (2). A flat plate (5) is pressed against the membrane (3) to rupture the membrane where it covers the projection (4) to expose the projection (4). The projection (4) is then etched.

IPC 1-7

H01L 21/302

IPC 8 full level

H01L 21/306 (2006.01); **H01L 21/205** (2006.01); **H01L 21/302** (2006.01); **H01L 21/3065** (2006.01); **H01L 21/308** (2006.01)

CPC (source: EP US)

H01L 21/02381 (2013.01 - EP US); **H01L 21/02532** (2013.01 - EP US); **H01L 21/0262** (2013.01 - EP US); **H01L 21/3086** (2013.01 - EP US); **Y10S 438/942** (2013.01 - EP US)

Citation (search report)

- US 3718514 A 19730227 - ERDMAN W, et al
- DE 2104671 A1 19710930 - IBM
- US B563722 I5 19760113
- DE 2517159 B2 19770217

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